

IN THE CLAIMS

1. (Currently Amended) A magnetic memory device constructed as a magnetic random access memory, said magnetic memory device comprising:

a memory element having by laminating a magnetization pinned layer in which the orientation of magnetization is pinned and a magnetic layer in which the orientation of magnetization is changeable, and

a magnetic shield layer for magnetically shielding said memory element, said memory element disposed in a position so as to avoid inward from an edge portion of said magnetic shield layer toward a center portion of said magnetic shield layer, and outward from and a said center portion of said magnetic shield layer toward said edge portion.

2. (Currently Amended) A magnetic memory device comprising:

a memory element having a magnetic layer capable of being magnetized, and

a magnetic shield layer for magnetically shielding said memory element,

said memory element disposed in a position so as to avoid inward from an edge portion of said magnetic shield layer toward a center portion of said magnetic shield layer, and outward from and a said center portion of said magnetic shield layer toward said edge portion.

3. (Currently Amended) ~~A magnetic memory device according to claim 1 or claim 2,~~ A magnetic memory device constructed as a magnetic random access memory, said magnetic memory device comprising:

a memory element having a magnetization pinned layer in which the orientation of magnetization is pinned, and a magnetic layer in which the orientation of magnetization is changeable; and

a magnetic shield layer for magnetically shielding said memory element, said memory element disposed so as to avoid an edge portion and a center portion of said magnetic shield layer;

wherein said memory element is disposed in a region between a position at 0.1 L inward from one side of said ~~magnet~~magnetic shield layer and a position at 0.15 L outward

from the center of said magnetic shield layer toward one side thereof, where a length from one side of said magnetic shield layer to an opposed side thereof is L.

4. (Currently Amended) A memory device according to claim 3 or 11, wherein said memory element is disposed in a region between a position at 0.2 L inward from said one side and a position at 0.15 L outward from the center of said shield layer toward said one side thereof, where said magnetic shield layer is provided on both sides of said memory element, and a distance between said magnetic shield layers, a length from said one side of said magnetic shield layer to the opposed side thereof, and an external magnetic field to be applied are constant respectively.

5. (Currently Amended) A memory device according to claim 3 or 11, wherein said memory element is disposed in a region between a position at 0.1 L inward from said one side thereof and a position at 0.2 L outward from the center of the shield layer toward said one side thereof, where a distance between said magnetic shield layers, a thickness of said magnetic shield layers, and an external magnetic field to be applied are constant respectively.

6. (Original) A memory device according to claim 1 or claim 2, wherein said magnetic shield layer is disposed on the top and/or bottom of a package having by sealing said memory element therein, or/and on the upper portion and/or the lower portion of said memory element within said package.

7. (Original) A memory device according to claim 6, wherein said memory element is present almost all over said package.

8. (Original) A memory device according to claim 1 or claim 2, wherein said magnetic shield layer is in the form of a flat film or plate, or having concave and/or convex portions thereon, or through-holes such as mesh or slits.

9. (Currently Amended) ~~A memory device according to claim 6,~~ A magnetic memory device constructed as a magnetic random access memory, said magnetic memory device comprising:

a memory element having a magnetization pinned layer in which the orientation of magnetization is pinned, and a magnetic layer in which the orientation of magnetization is changeable; and

a magnetic shield layer for magnetically shielding said memory element, said memory element disposed so as to avoid an edge portion and a center portion of said magnetic shield layer;

wherein said magnetic shield layer is disposed on the top and/or bottom of a package having by sealing said memory element therein, or/and on the upper portion and/or the lower portion of said memory element within said package, and wherein said magnetic shield layer is formed of soft magnetic material that exhibits saturation magnetism at 1.8 tesla or more.

10. (Original) A memory device according to claim 1, wherein said memory device is constructed such that an insulating material layer or a conductive material layer is sandwiched between said magnetization pinned layer and said magnetic layer, that with a magnetic field induced by passing a respective current through wirings provided on the top and the bottom of said memory element, the orientation of magnetization in said magnetic layer is aligned in a prescribed direction thereby writing information thereto, and that said written information is read out by use of the tunnel magnetoresistance effect between said wirings.

11. (New) A magnetic memory device comprising:

a memory element having a magnetic layer capable of being magnetized; and

a magnetic shield layer for magnetically shielding said memory element;

wherein said memory element is disposed so as to avoid an edge portion and a center portion of said magnetic shield layer, and wherein said memory element is disposed in a region between a position at $0.1 L$ inward from one side of said magnetic shield layer and a position at $0.15 L$ outward from the center of said magnetic shield layer toward one side thereof, where a length from one side of said magnetic shield layer to an opposed side thereof is L .

12. (New) A magnetic memory device comprising:

a memory element having a magnetic layer capable of being magnetized; and

a magnetic shield layer for magnetically shielding said memory element;
wherein said memory element is disposed so as to avoid an edge portion and a center portion of said magnetic shield layer, wherein said magnetic shield layer is disposed on the top and/or bottom of a package having by sealing said memory element therein, or/and on the upper portion and/or the lower portion of said memory element within said package, and wherein said magnetic shield layer is formed of soft magnetic material that exhibits saturation magnetism at 1.8 tesla or more.